

## DECLARATION FOR PATENT APPLICATION

As a below-named inventor, I hereby declare that this declaration is for the national phase of the PCT

My residence, post office address and citizenship are as stated below, next to my name. I believe I am an original, first and joint inventor of the subject matter which is claimed and for which a patent is sought on the invention entitled: NITRIDE SEMICONDUCTOR DEVICE AND MANUFACTURING METHOD THEREOF. The specification of which was described and claimed in PCT International Application No. \_\_\_\_\_ filed on \_\_\_\_\_. I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above. I acknowledge the duty to disclose information which is material to the examination of this application in accordance with Title 37, Code of Federal Regulations, Section 1.56(a).

I hereby claim foreign priority benefits under Title 35, United States Code, § 119 of any foreign application(s) for patent or inventor's certificate or any PCT International application(s) designating at least one country other than the United States listed below and have also identified below any foreign application for patent or inventor's certificate or any PCT International application(s) designating at least one country other than the United States filed by me on the same subject matter having a filing date before that of the application on which priority is claimed

Prior Foreign Application(s)			Priority Claim	
			Yes	No
P 11-030990	Japan	09/02/1999	X	
Number	Country	Day/Month/Year Filed		
P 11-331797	Japan	22/11/1999	X	
Number	Country	Day/Month/Year Filed		

I hereby claim the benefit under Title 35, United States Code, § 120 of any United States application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code, § 112, I acknowledge the duty to disclose material information as defined in Title 37, Code of Federal Regulations, § 1.56(a) which occurred between the filing date of the prior application and the national or PCT international filing date of this application:

Application Serial No	Filing Date	Status: Patented, Pending, Abandoned
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I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Full Name of First Joint Inventor: Shinichi NAGAHAMA

Inventor's Signature: *Shinichi Nagahama* December 24, 1999

Date

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Full Name of Second Joint Inventor: Shuji NAKAMURA

Inventor's Signature: *Shuji Nakamura* December 24, 1999

Date

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: ) Group:  
Shinichi NAGAHAMA et al. ) Art Unit:  
 ) Examiner:  
Serial No.: )  
 )  
Filed: ) POWER OF ATTORNEY BY ASSIGNEE  
 )  
For: NITRIDE SEMICONDUCTOR DEVICE AND )  
MANUFACTURING METHOD THEREOF )

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Nichia Corporation, Assignee of the above-identified  
application by Assignment dated 24/12/1999 hereby appoints the members of the firm of  
HAVERSTOCK & OWENS LLP, a firm including Thomas B. Haverstock (Reg. No. 32,571) and Jonathan O.  
Owens (Reg. No. 37,902) 260 Sheridan Avenue, Suite 420, Palo Alto, California 94306, telephone: (650) 833-  
0160, facsimile: (650) 833-0170, as its attorneys with full power of substitution to prosecute this application and  
to transact all business in the Patent and Trademark Office in connection therewith.

Please direct all correspondence regarding this application to the following:

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I hereby certify that the Assignment document filed with the application or filed subsequent to the filing  
date of the application, has been reviewed and I hereby certify that, to the best of my knowledge and belief, title  
is with \_\_\_\_\_.

Dated: February 3, 2000

By: Eiji Ogawa  
Name: Eiji OGAWA  
Title: President